AMENDMENTS TO THE CLAIMS

Please cancel Claims 1-13, 16-24, 27, 28 and 37-39 and add new Claim 40 as follows.

LISTING OF CLAIMS

1.-28. (cancelled)

29. (original) A semiconductor device comprising:

an insulated gate transistor disposed in a current path of an electric load;

a gate voltage boosting element having one end connected to a gate electrode of said insulated gate transistor so as to operate in response to a surge applied from a high-voltage terminal of said insulated gate transistor;

a wiring member serving as a parasitic inductance against the applied surge, said wiring member being connected in parallel with said gate voltage boosting element with respect to the high-voltage terminal of said insulated gate transistor,

wherein said insulated gate transistor and said gate voltage boosting element are formed in a chip, and said wiring member is provided outside said chip.

30. (original) The semiconductor device in accordance with claim 29, wherein said wiring member is a bonding wire.

31. (original) The semiconductor device in accordance with claim 29, wherein said chip is a resin molded chip mounted on a printed circuit board, and said wiring member is a combination of a bonding wire, a lead frame, and

a conductive pattern formed on said printed circuit board.

32. (original) The semiconductor device in accordance with claim 29, wherein

said chip is mounted on a semiconductor substrate by using the flip chip bonding method, and

said wiring member is a conductive pattern formed on said semiconductor substrate.

33. (original) The semiconductor device in accordance with claim 29, wherein said gate voltage boosting element is a Zener diode.

34. (original) The semiconductor device in accordance with claim 29, wherein said gate voltage boosting element is a combination of a plurality of circuit elements selected from the group consisting of a Zener diode, a bipolar transistor, and a metal oxide semiconductor transistor.

35. (original) The semiconductor device in accordance with claim 29, wherein said gate voltage boosting element is a combination of a plurality of circuit elements selected from the group consisting of a capacitor, a bipolar transistor, and a metal oxide semiconductor transistor.

36. (original) The semiconductor device in accordance with claim 29, wherein said gate voltage boosting element is a set of a capacitor and a Zener diode.

37.-39. (cancelled)

40. (new) The semiconductor device in accordance with claim 29, wherein said gate voltage boosting element includes a series of a metal oxide semiconductor transistor and a back-flow preventing Zener diode connected between said high-voltage terminal and said gate electrode of said insulated gate transistor, and a capacitor connected between said high-voltage terminal of said insulated gate transistor and a gate electrode of said metal oxide semiconductor transistor.